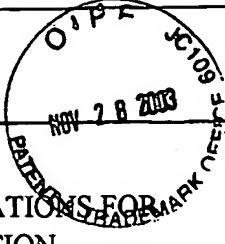
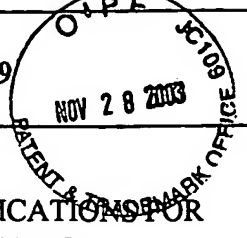


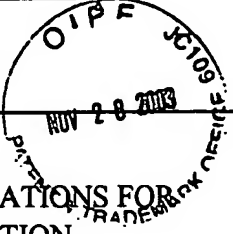
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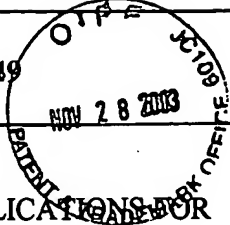
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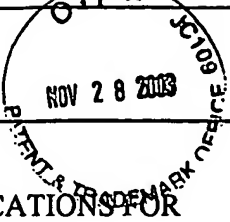
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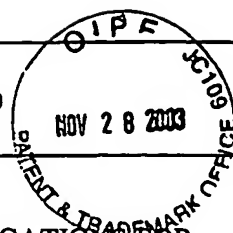
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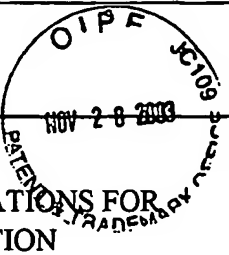
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	Filing Date: June 27, 2003	Group Art: unknown <i>2828</i>

TN		U.S. Patent Application Serial No. 09/751,422, filed December 29, 2000, entitled "Resonant Reflector for Use with Optoelectronic Devices".
		U.S. Patent Application Serial No. 09/751,423, filed December 29, 2000, entitled "Spatially Modulated Reflector for an Optoelectronic Device".

EXAMINER: <i>Tuan Nguyen</i>	DATE CONSIDERED: <i>5/10/05</i>
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.